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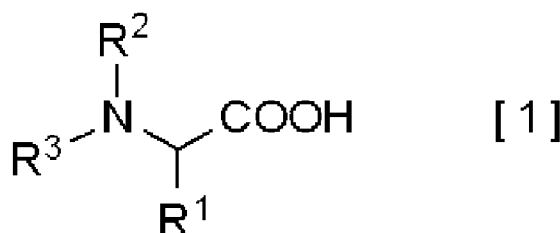
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(54) Title: SUBSTRATE CLEANER FOR COPPER WIRING, AND METHOD FOR CLEANING COPPER WIRING SEMICONDUCTOR SUBSTRATE

(54) 発明の名称: 銅配線用基板洗浄剤及び銅配線半導体基板の洗浄方法



(57) Abstract: The present invention addresses the problems of: providing a substrate cleaner for copper wiring which sufficiently suppresses the elution of metal copper during the cleaning of a semiconductor substrate after the chemical mechanical polishing (CMP) step in a process for manufacturing the semiconductor substrate, and which permits the removal of particles and impurities such as copper (II) hydroxide and copper (II) oxide generated during the chemical mechanical polishing step (CMP); and of providing a method for cleaning a copper wiring semiconductor substrate characterized by the use of this substrate cleaner for copper wiring. The present invention relates to a substrate cleaner for copper wiring comprising an aqueous solution containing [I] an amino acid represented by General Formula (1), and [II] an alkylhydroxylamine; and to a method for cleaning a copper wiring semiconductor substrate characterized by the use of this substrate cleaner for copper wiring. (In the formula, R¹ represents a hydrogen atom, a carboxymethyl group, or a carboxyethyl group; and R² and R³ each independently represent a hydrogen atom, or a C₁₋₄ alkyl group which may have a hydroxyl group. R¹ to R³ cannot all be hydrogen atoms.)

(57) 要約:

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